Supplementary Materials: 320-nm Flexible Solution-Processed 2,7-dioctyl[1] benzothieno[3,2-b]benzothiophene Transistors

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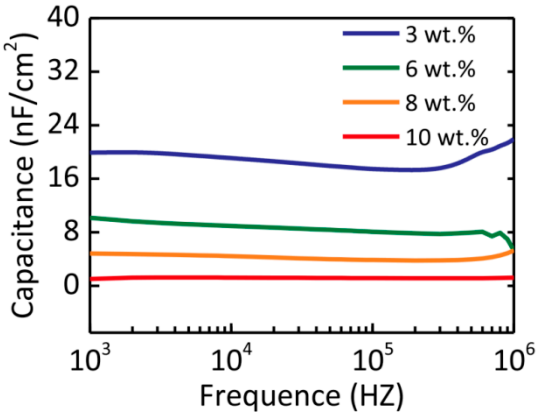

Figure S1. Dependence of the capacitance with frequency of the PVA dielectric layer spun from solution of different concentrations (3 wt %, 6 wt %, 8 wt % and 10 wt %).

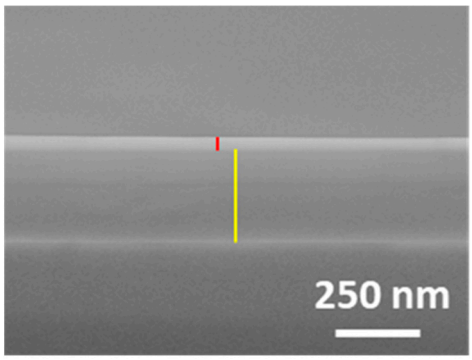

Figure S2. The cross-sectional SEM image of the device. The red line indicates "S/D electrode (20 nm) + C8-BTBT (~20 nm)" layer and the yellow line indicates the PVA layer (~ 280 nm) with gate electrode embed in it.

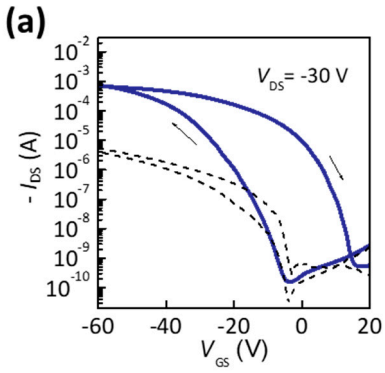

Figure S3. (**a**) Transfer curves swept in backward and forward directions of the C8-BTBT OTFT with PVA dielectric layer.

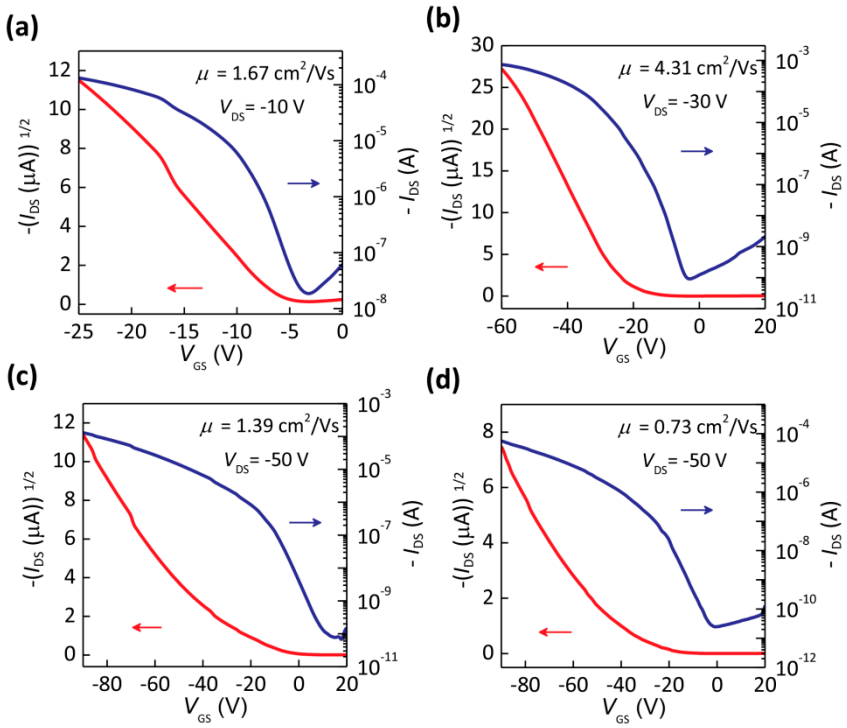

Figure S4. (**a–d**) The transfer characteristics of C8-BTBT OTFTs with PVA dielectric layer spun from solution of different concentrations (3 wt %, 6 wt %, 8 wt % and 10 wt %).

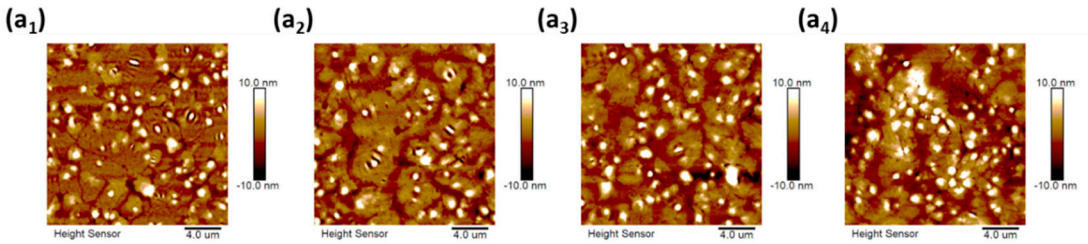

Figure S5. (**a1-a4**) AFM images of the C8-BTBT films on the corresponding PVA films spun from different concentrations (3 wt %, 6 wt %, 8 wt % and 10 wt %).